

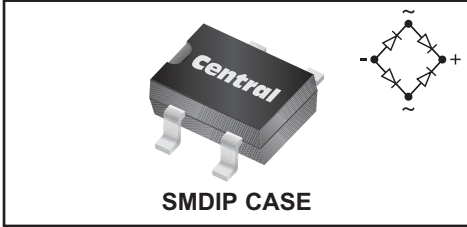
CBRSDSH2-40
SURFACE MOUNT
2 AMP SILICON
SCHOTTKY BRIDGE RECTIFIER



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CBRSDSH2-40 is a full wave bridge rectifier mounted in a durable epoxy surface mount case, utilizing glass passivated chips.



MARKING: FULL PART NUMBER

FEATURES:

- Low Leakage Current (40 μ A TYP @ V_{RRM})
- High 2.0A Current Rating
- Low V_F Schottky Diodes (400mV TYP @ $I_F=2.0A$)

MAXIMUM RATINGS: ($T_A=25^\circ C$)

Peak Repetitive Reverse Voltage
DC Blocking Voltage
RMS Reverse Voltage
Average Forward Current
Peak Forward Surge Current (8.3ms)
Operating and Storage Junction Temperature
Typical Thermal Resistance (Note 1)
Typical Thermal Resistance

SYMBOL

V_{RRM} 40
 V_R 40
 $V_{R(RMS)}$ 28
 I_O 2.0
 I_{FSM} 110
 T_J, T_{stg} -50 to +125
 θ_{JA} 40
 θ_{JL} 15

UNITS

V
V
V
A
A
 $^\circ C$
 $^\circ C/W$
 $^\circ C/W$

ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^\circ C$ unless otherwise noted)

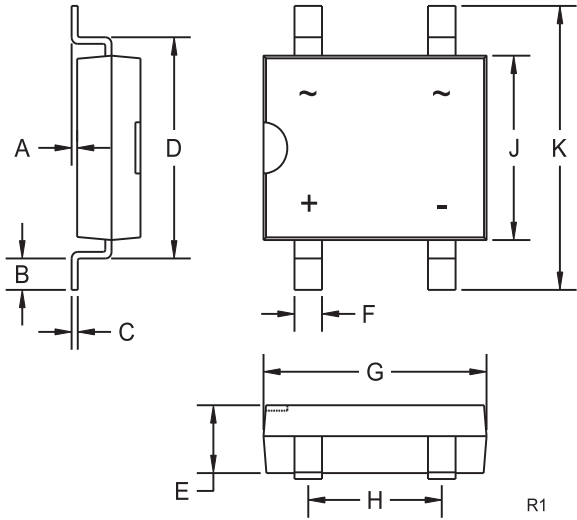
SYMBOL	TEST CONDITIONS	TYP	MAX	UNITS
I_R	$V_R=40V$	40	70	μA
V_F	$I_F=2.0A$	400	450	mV
C_J	$V_R=4.0V, f=1.0MHz$	400	500	pF

Notes: (1) Devices mounted on PCB with 13mm x 13mm copper pads.

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SMDIP CASE - MECHANICAL OUTLINE



DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.008	0.10	0.20
B	0.040	0.060	1.02	1.52
C	0.009		0.23	
D	0.290	0.310	7.37	7.87
E	0.086	0.098	2.18	2.49
F	0.038	0.042	0.97	1.07
G	0.316	0.335	8.03	8.51
H	0.195	0.205	4.95	5.21
J	0.245	0.255	6.22	6.48
K	0.360	0.410	9.14	10.41

SMDIP (REV: R1)

MARKING: FULL PART NUMBER

R1 (26-October 2011)

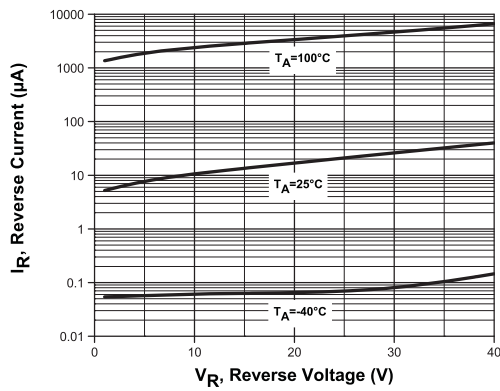
CBRSDSH2-40



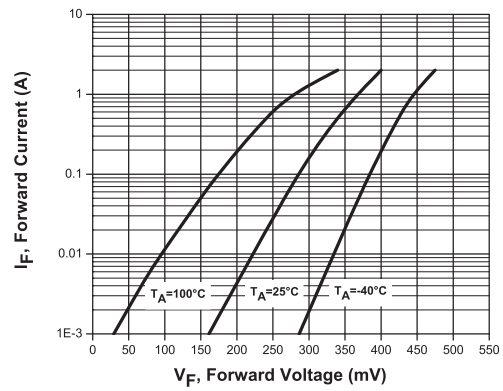
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TYPICAL ELECTRICAL CHARACTERISTICS

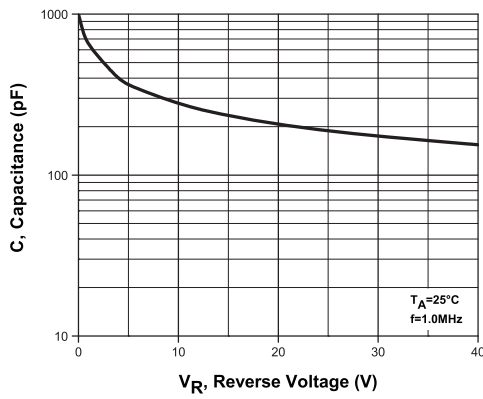
Typical Per Diode Leakage Current



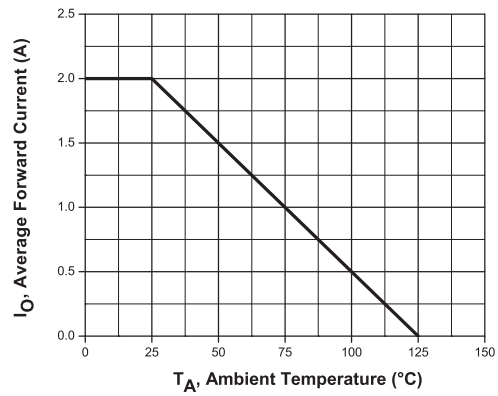
Typical Per Diode Forward Voltage



Typical Per Diode Capacitance



Per Diode Current Derating



R1 (26-October 2011)